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FORM PTO-1449 — U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

LIST OF REFERENCES CITED BY APPLICANT

(Use several sheets if necessary)

ATTY. DOCKET NO.	SERIAL NO
107317-00039	Div. of 08/787,451
APPLICANT: HASHIMOTO et al.	
FILING DATE: Herewith	GROUP: 2823

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NO.	DATE	NAME	CLASS	SUB-CLASS	FILING DATE
K.N.	AA	4,563,367	1/7/86	SHERMAN	156	643	
K.N	AB	4,564,997	1/21/86	MATSUO ET AL.	156	647	
K.N.	AC	5,016,564	5/21/91	NAKAMURA ET AL.	156	345	
K.N	AD	4,960,073	10/2/90	SUZUKI ET AL.	156	345	
K.N.	AE	5,022,977	6/11/91	MATSUOKA ET AL.			
K.N.	AF	5,259,922	11/9/93	YAMMNO ET AL.	156	643	

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		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION YES	NO	PART.
K.N.	AG	5-90224	4/9/93	JAPAN					
K.N	AH	60/117723	6/25/85	JAPAN					
K.N	AI	4-340717	11/27/92	JAPAN					
K.N	AJ	2-94628	4/5/90	JAPAN	156	345			
K.N	AK	1-14920	1/19/89	JAPAN	156	345			
K.N	AL	1-32631	2/2/89	JAPAN	156	345			

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K.N.	AM	N. Jiwari et al., Japan J. Appl. Phys. 32(6b) 3019 "Al etching...helicon wave plasma", 6/1993.
K.N	AN	Y. Ra et al., J. Vac. Sci. Technol. 11(6) 2911 :Direct currect bias...transformer coupled plasma etcher, 11/1993.
K.N.	AO	M.W. Horn et al., Optical Eng.32(10) 2388 "Comparison of etching tools...", 10/1993.

EXAMINER	DATE CONSIDERED
K Nguyen	12/5/02

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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K.N.	AA	5,344,536	9/6/94	OBUCHI et al..	156	643	
K.N.	AB	5,156,703	10/20/92	OECHSNER	156	643	
K.N.	AC	5,183,777	2/2/93	DORI et al.	437	225	
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K.N	AE	5,290,382	3/1/94	ZAROWIN et al.	204	298	
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K.N	AG	04-354124	12/8/92	JAPAN					
K.N	AH	5-234955	9/10/93	JAPAN	216	70			
K.N.	AI	63-43324	2/24/88	JAPAN	156	345			
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K.N.	AM	"Charging Damage to Gate Oxides in a O_2 Magnetron Plasma", Fang et al., J. Appl. Phys., Vol. 72, No. 10, November 15, 1992, pgs 4865-4872.
K.N	AN	H. Nihei et al., Rev. Sci. Instrum., 63 (3) March 1992, pgs. 1932, "....Plasma source using an axial mirror and multiple fields".
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K.N	AA	5,368,685	11/29/94	KUMIHASHI et al.	216	70	
K.N	AB	4,971,651	11/20/90	WATANABE et al.	216	70	
K.N	AC	5,350,710	9/27/94	HONG et al.	156	643	
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K.N	AO	S. Samukawa et al., J. Vac Sci. Technol, B93 (1991) 1471 "400 KMZ RF biased ECR plasma etching for ...."

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K.N.	AM	S. Samukawa, Japan J. Appl. Phys. 30, 11B (1991) 3154 "400 KHZ RF biased ECR resonance position etching".
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